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DATE: April 2, 2002

SHEET 1 of 1

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## Form PTO - 1449 (M dified)

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE  
(Modified) PATENT AND TRADEMARK OFFICE

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SERIAL NO.

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INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

(Use several sheets if necessary)

(37 CFR 1.98 (b))

APPLICANT

R. Ugajin

FILING DATE

April 2, 2002

GROUP

Not yet assigned

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE

## FOREIGN PATENT OR PUBLISHED FOREIGN PATENT APPLICATION

		DOCUMENT NUMBER	PUBLIC- ATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUB CLASS	TRANS- LATION
							YES NO
B1	1	1 1 9 5 8 0 1	21.07.99	JP			*
B2	2001	1 1 8 3 7 9	27.04.01	JP			*

\*abstract only

## OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)

C1	H. Isshiki, K. Tanaka and T. Kimura, "Conduction subband formation in (GaSa)m(GaP)n FRACTAL structured atomic-layer-superlattice grown by atomic layer epitaxy", Proc. of the 24 <sup>th</sup> International Conference on The Physics of Semiconductors, CD-ROM File No. 0948, World Scientific Publishing Co. (1999)
C2	R. Ugajin, "Composite nanomaterials based on fractal-shaped structures", Physics Letters A, 227, (2000) Pages 267 to 272.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial citation c nsidered. Draw line thr ough citation if n t in conformance and not c nsidered. Include copy f this form with next communicati n to applicant.

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